



60V P-Channel Enhancement Mode MOSFET

Voltage

-60 V

Current

-11.5 A

Features

- R_{DS(ON)}, V_{GS}@-10V, I_D@-6A<110mΩ
- $R_{DS(ON)}$, V_{GS} @-4.5V, I_{D} @-3A<130m Ω
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN5060-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0028 ounces, 0.08 grams

DFN5060-8L

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

				1	
PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V_{DS}	-60	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T _C =25°C	- I _D	-11.5		
	T _C =100°C		-7.2	Α	
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	-35		
Power Dissipation	T _C =25°C	Po	26	W	
	T _C =100°C		10		
Continuous Drain Current (Note 4)	T _A =25°C	I _D	-3.2	Α	
	T _A =70°C		-2.5		
Power Dissipation	T _A =25°C	Po	2	W	
	T _A =70°C		1.3		
Single Pulse Avalanche Energy (Note 6)		E _{AS}	20	mJ	
Operating Junction and Storage Temperature Range		T_{J} , T_{STG}	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	4.8	°C/W	
	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V, I_D =-250uA	-60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=-250uA$	-1	-1.7	-2.5	
Drain-Source On-State Resistance	R _{DS(on)}	V_{GS} =-10V, I_D =-6A	-	87	110	mΩ
		V_{GS} =-4.5V, I_{D} =-3A	-	110	130	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} =-60V, V_{GS} =0V	-	-	-1	uA
Gate-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	<u>+</u> 100	nA
Dynamic (Note 7)						
Total Gate Charge	Qg	V_{DS} =-30V, I_{D} =-4A, V_{GS} =-10V (Note 2,3)	-	10	-	nC
Gate-Source Charge	Q_{gs}		-	1.6	-	
Gate-Drain Charge	Q_{gd}		-	3	-	
Input Capacitance	Ciss	V _{DS} =-30V, V _{GS} =0V,	-	785	-	pF
Output Capacitance	Coss		-	175	-	
Reverse Transfer Capacitance	Crss	f=1MHZ	-	112	-	
Turn-On Delay Time	td _(on)		-	8	-	ns
Turn-On Rise Time	t _r	$\begin{array}{c} V_{DS}\text{=-}30\text{V}, \; R_{L}\text{=}30\Omega, \\ V_{GS}\text{=-}10\text{V}, \; R_{G}\text{=}6.2\Omega \\ \text{(Note 2,3)} \end{array}$	-	15	-	
Turn-Off Delay Time	td _(off)		-	43	-	
Turn-Off Fall Time	t _f		-	8.4	-	
Drain-Source Diode						
Maximum Continuous Drain-Source			-	-	-11.5	А
Diode Forward Current	I _S					
Diode Forward Voltage	V_{SD}	I _S =-1A, V _{GS} =0V	-	-0.76	-1	V

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{0JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =-20A, V_{DD} =-25V, V_{GS} =-10V.
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

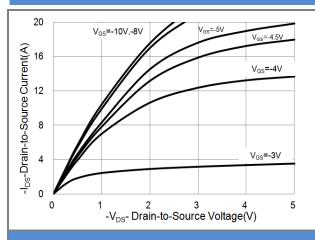


Fig.1 Output Characteristics

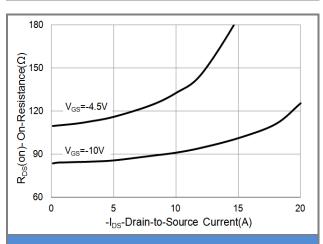


Fig.3 On-Resistance vs. Drain Current

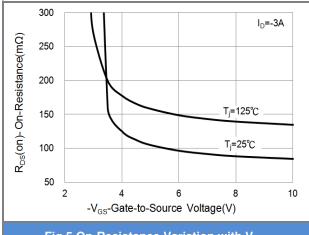


Fig.5 On-Resistance Variation with V_{GS}

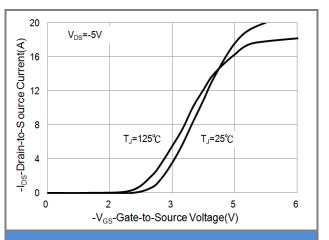


Fig.2 Transfer Characteristics

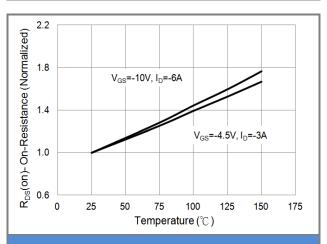


Fig.4 On-Resistance vs. Junction temperature

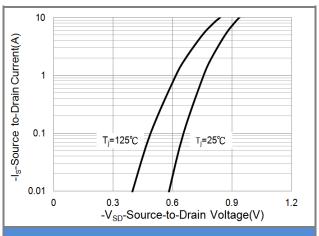


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

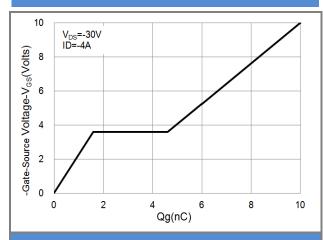


Fig.7 Gate-Charge Characteristics

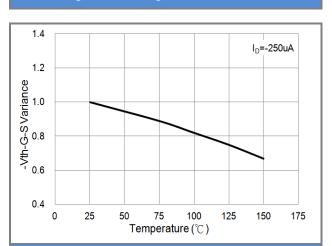
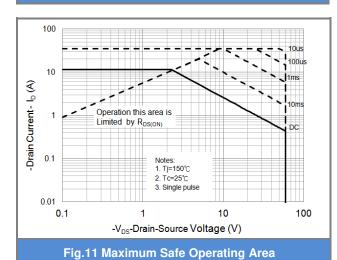


Fig.9 Threshold Voltage Variation with Temperature



1.1 I_D=-250uA I

Fig.8 Breakdown Voltage Variation vs. Temperature

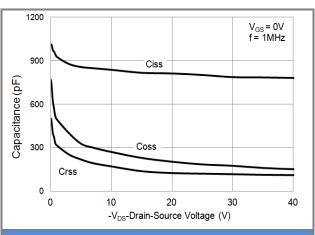


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

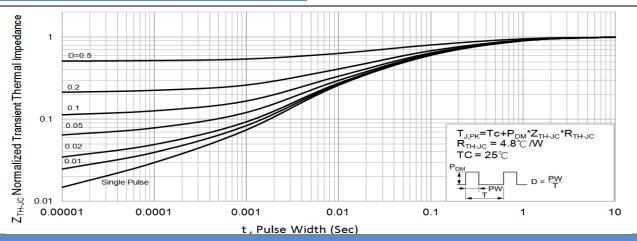


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

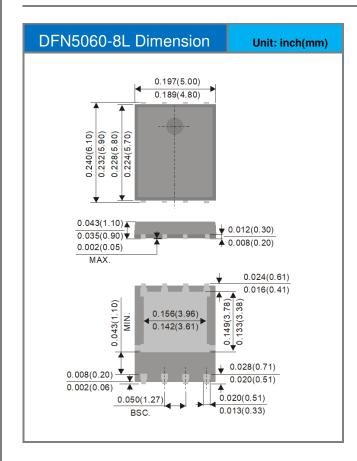


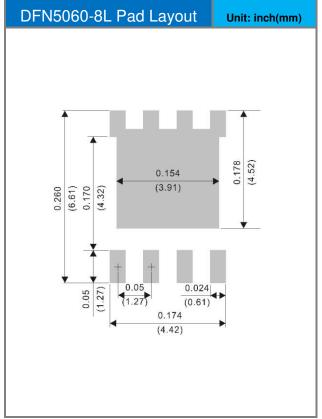


Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ5461A-AU_R2_000A1	DFN5060-8L	3000pcs / 13" reel	Q5461A	Halogen free

Packaging Information & Mounting Pad Layout









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